U.S. PTO 12/318392 12/29/2008

RECORDATION FORM COVER

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01-13-2009

PATENTS	103543326
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Name of conveying party(ies):	2. Name and address of receiving party(les)
Jung Goo Park	Name: MagnaChip Semiconductor, Ltd.
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Additional name(s) of conveying party(ies) attached? Yes X No	Street Address:
3. Nature of conveyance/Execution Date(s):	
Execution Date(s): December 17, 2008	1 Hyangjeong-dong, Heungduk-gu,
X Assignment Merger Change of Name	
Security Agreement Joint Research Agreement	City: Cheongju-Si
Government Interest Assignment	State: Chungcheongbuk-do
Executive Order 9424, Confirmatory License	Country: Republic of Korea Zip: 361-725
Other	Additional name(s) & address(es) Yes X No
	attached?
A. Patent Application No.(s)	B. Patent No.(s)
Additional numbers attached?	Yes x No
5. Name and address to whom correspondence concerning document should be mailed:	6. Total number of applications and patents involved:
Name: Collin W. Park MORGAN LEWIS & BOCKIUS LLP	7. Total fee (37 CFR 1.21(h) & 3.41) \$ 40.00
Internal Address: Atty. Dkt.: 064991-5031US	
Street Address: 1111 Pennsylvania Ave NW	X Authorized to be charged to deposit account
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	None required (government interest not affecting title
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Calli W Pul	December 29, 2008
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Collin W. Park - 43,378 Name of Person Signing	Total number of pages including cover sheet, attachments, and documents: 2
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DB1/62434520.1

PATENT REEL: 022097 FRAME: 0599

ATTORNEY DOCKET NO.:

SOLE/JOINT INVENTION (U.S. Rights Only)

ASSIGNMENT

WHEREAS I/We, the below named inventor(s), [hereinafter referred to as Assignor(s)], have made an invention entitled:

Method for forming gate oxide of semiconductor device		
or filed an		
hose post ereinafter invention, upon this		
of which nd set over, igns, isions, and and all emarks of igns, in		
deration, his execute said us, make s, to obtain that any and assigns.		
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2006		
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RECORDED: 12/29/2008

PATENT REEL: 022097 FRAME: 0600